








	<h2 style="color: red;">FQB5N30TM</h2>	
	Hersteller-Teilenummer:	FQB5N30TM
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	MOSFET N-CH 300V 5.4A D2PAK
Datenblätter:	 FQB5N30TM.pdf	
RoHS Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 1450 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
Image may be representation. See specs for product details.		

Spezifikationen

Teilenummer	FQB5N30TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 300V 5.4A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1450 pcs Stock
detaillierte Beschreibung	N-Channel 300V 5.4A (Tc) 3.13W (Ta), 70W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 70W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	300V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	5.4A (Tc)
Rds On (Max) @ Id, Vgs	900 mOhm @ 2.7A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	13nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	430pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)















































FQB5N30TM ist neu im Original, Suche FQB5N30TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB5N30TM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB5N30TM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB5N40 Fairchild/ON Semiconductor FQB5N40 FAIRCHILD</p>	 <p>FQB5N20LTM AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK</p>	 <p>FQB5N30TM Fairchild/ON Semiconductor MOSFET N-CH 300V 5.4A D2PAK</p>	 <p>FQB5N20LTM Fairchild/ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK</p>
 <p>FQB5N20TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK</p>	 <p>FQB5N20TM Fairchild/ON Semiconductor MOSFET N-CH 200V 4.5A D2PAK</p>	 <p>FQB5N50 FAIRCHILD FQB5N50 FAIRCHILD</p>	 <p>FQB5N50C FAIRCHI FQB5N50C FAIRCHI</p>

heiße Teile

Mehr

 FQB4N50TM	 FQB4N50TM	 FQB4N60C	 FQB4N80TM	 FQB4N80TM
 FQB4N90TM	 FQB4N90TM	 FQB4P25TM	 FQB4P25TM	 FQB50N03
 FQB50N06	 FQB50N06C	 FQB50N06L	 FQB50N06LTM	 FQB50N06LTM
 FQB50N06M	 FQB50N06TM	 FQB50N06TM	 FQB50N06TM-NL	 FQB55N06TM
 FQB55N06TM	 FQB55N10	 FQB55N10TM	 FQB55N10TM	 FQB5N20L
 FQB5N30TM	 FQB5N50C	 FQB5N50CF	 FQB5N50CTM	 FQB5N50CTM
 FQB5N60CTM	 FQB5N60CTM	 FQB5N90TM	 FQB5N90TM	 FQB5P10TM
 FQB5P10TM	 FQB630TM	 FQB630TM	 FQB65N06	 FQB65N06TM
 FQB65N06TM	 FQB6N40C	 FQB6N40CF	 FQB6N40CTM	 FQB6N40CTM
 FQB6N50TM	 FQB6N50TM	 FQB6N60C	 FQB6N60CTM	 FQB6N60CTM

Contact us:Info@Y-IC.com

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